

$$n_i = B T^{3/2} e^{-E_g/2kT}$$

$$n_i^2 = n_b p_0$$

$$N_d \gg n_i \Rightarrow$$

$$\begin{aligned} n_o &= N_d \\ p_0 &= \frac{n_i^2}{N_d} \end{aligned}$$

$$N_a \gg n_i$$

$$\Rightarrow p_0 = N_a$$

$$n_o = \frac{n_i^2}{N_a}$$

- Drift current:

n-type:

$$V_d = -M_n \vec{E}$$

$$\vec{J}_n = -e n_o V_d$$

$$J_n = +e n_o M_n \vec{E}$$

p-type:

$$V_d = M_p \vec{E}$$

$$\vec{J}_p = e p_o V_d$$

$$\vec{J}_p = e p_o M_p \vec{E}$$

take $e = 1.6 \times 10^{-19}$

$$\vec{J}_{\text{total}} = \vec{J}_n + \vec{J}_p \Rightarrow \vec{J} = \sigma \vec{E}$$

$$\sigma = \frac{1}{p}$$

- Diffusion Current:

n-type:

$$\vec{J}_n = e D_n \frac{d n_o}{dx}$$

p-type:

$$\vec{J}_p = -e D_p \frac{d p_o}{dx}$$

$\Rightarrow \frac{dn_o}{dx}, \frac{dp_o}{dx}$ found from slope in a graph
or from a function $n_o = f(x)$
 $p_o = f(x)$

$$\frac{D_n}{M_n} = \frac{D_p}{M_p} = V_T = \frac{kT}{e} = 0.026 \text{ volt}$$

at room temp.
300 K

$$V_{bi} = V_T \ln \left(\frac{N_d N_a}{n_i^2} \right)$$

(2)

* Pn-junction:

* Reverse: $I_D = 0$

$$C_j = C_{j_0} \left(1 + \frac{V_R}{V_{bi}} \right)^{-\frac{1}{2}}$$

junction capacitance. reverse voltage.

* Forward:

$$I_D = I_s \left[e^{\frac{V_D}{n k_T}} - 1 \right]$$

if \underline{n} not given assume $n=1$

* Diode:

$$V_D = V_g + I_D R_D$$

- DC Analysis:

① assume O.C.

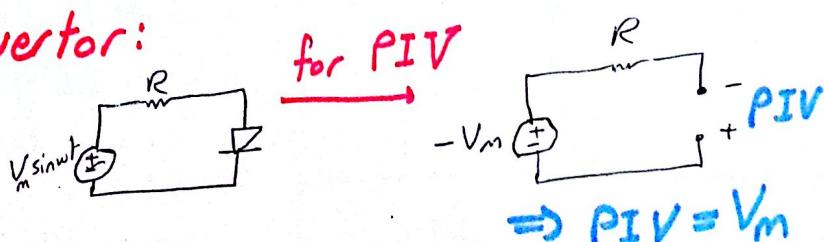
② find V_D .

③ $V_D < V_g$ "right assumption"
off
 $\rightarrow I_D = 0$, V_D found in ②

$V_D > V_g$ "wrong assumption"
ON
 $V_D = V_g + I_D R_D$

* AC to DC converter:

$$\frac{V_L}{V_S \text{ (rms)}} = \frac{N_1}{N_2}$$



as well as we can find PIV for Bridge & centre tapped.

$$V_{(rms)} = \frac{V_m}{\sqrt{2}}$$

- filter circuit:

$$V_r = V_m - V_L$$

Pipple Voltage.

$$V_r = \frac{V_m T_p}{R C}$$

(3)

- for halfwave:

$$V_M = V_m - V_8$$

$$T_P = T_S = \frac{1}{f_S}$$

$$V_r = \frac{V_m - V_8}{f_S RC}$$

- for fullwave:

Bridge

$$T_P = \frac{T_S}{2} = \frac{1}{2f_S}$$

Centre tapped

$$V_M = V_m - 2V_8$$

$$V_r = \frac{V_m - 2V_8}{2f_S RC}$$

$$V_M = V_m - V_8$$

$$V_r = \frac{V_m - V_8}{2f_S RC}$$

- H.W without filter:

$$V_{DC} = \frac{V_M}{\pi}$$

- F.W // // :

$$V_{DC} = \frac{2V_M}{2}$$

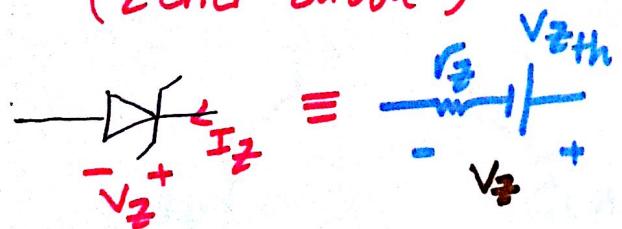
- H.W & F.W with filter:

$$V_{DC} = V_M - \frac{1}{2}V_r$$

* ripple factor = $\frac{V_r}{V_{DC}} * 100\%$

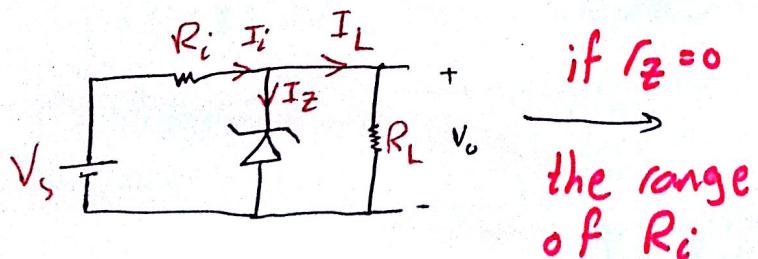
with filter

* Voltage Regulator:
(Zener diode)



$$\Rightarrow V_Z = V_{Z_{th}} + I_Z r_Z$$

$$\Rightarrow P_Z = I_Z V_Z$$



$$\frac{V_s - V_{Z_{th}}}{I_Z + I_L} \leq R_i \leq \frac{V_s - V_{Z_{th}}}{I_Z + I_L}$$

$$I_Z^{(max)} = \frac{I_L^{(max)} [V_s^{(max)} - V_{Z_{th}}] - I_L^{(min)} [V_s^{(min)} - V_{Z_{th}}]}{V_s^{(min)} - 0.9V_{Z_{th}} - 0.1V_s^{(max)}}$$

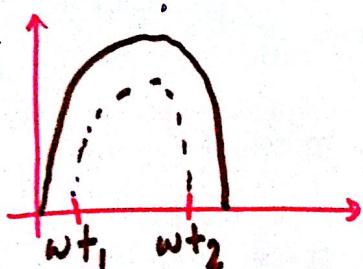
- Ideal Zener diode \Rightarrow source & load regulation = zero

- Non-ideal zener diode ($r_Z > 0$):

$$\text{source reg.} = \frac{\Delta V_L}{\Delta V_S} * 100\% \quad (\text{fixed } R_L)$$

$$\text{Load reg.} = \frac{V_L(\text{No load}) - V_L(\text{full load})}{V_L(\text{full load})} * 100\% \quad (\text{fixed } V_S)$$

* Battery charger:



$$\Rightarrow \text{The fraction of the cycle} = \frac{wt_2 - wt_1}{360^\circ} * 100\%$$

* Transistor:

- BJT:

$$I_E = I_B + I_C$$

$$I_C = \beta I_B$$

$$\alpha = \frac{\beta}{1+\beta}$$

$$\Rightarrow I_E = (1+\beta) I_B$$

$$\text{Power (P}_T\text{)} = I_C V_{CE}$$

* DC analysis:

① Assume forward-active mode

$$\Rightarrow \text{find } I_B, I_C, V_{CE}$$

Input loop

Output loop

$$\begin{aligned} V_{BE(\text{con})} &= 0.7 \text{ volt} \\ I_C &= \beta I_B \end{aligned}$$

$$\Rightarrow \text{if } V_{CE} > V_{CE(\text{sat})} \Rightarrow \text{right assumption.}$$

(2) otherwise, Assume Saturation mode

→ find I_B & I_C

↓
input
loop

↓
output
loop

$$V_{BE} = 0.7 \text{ volt}$$

ON

$$V_{CE} = V_{CE} = 0.2 \text{ or } 0.3 \text{ V}$$

(5)

⇒ if $I_C < \beta I_B$

⇒ right assumption.

(3) Otherwise, The mode of operation is Cutoff

$$I_B = I_C = I_E = 0$$

* Load line & Q-point values:

$$I_C \propto V_{CE}$$

$$I_{BQ}, I_{CQ}, V_{CEQ}$$

↳ the equation found from the output loop.

* Voltage transfer characteristic ($V_o \propto V_I$):

↳ we find the relation between V_o & V_I in the three modes (Forward / saturation / cutoff)

⇒ Then graph $V_o \propto V_I$.

* Biasing:

↳ voltage divider biasing:

$$R_{TH} = 0.1(1+\beta)R_E$$

"stability Rule"

we use also to find the highest value of R_E

⇒ sometimes we take it to check like that:

$$R_{TH} \ll (1+\beta)R_E$$

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* Early Effect:

- without early effect:

$$I_c = \beta I_s e^{\frac{V_{BE}}{V_T}}$$

- with early effect:

independent on V_{CE}

$$I_c = \beta I_s e^{\frac{V_{BE}}{V_T} \left(1 + \frac{V_{CE}}{V_A} \right)}$$

depend on V_{CE}

early effect voltage \Rightarrow

used in AC analysis

$$r_o = \frac{V_A}{I_{CQ}}$$

found in DC analysis.

* Leakage Current:

$$I_{CEO} = \frac{I_{CBO}}{1 - \alpha} = \beta I_{CBO}$$

I_{CBO} : emitter open circuit

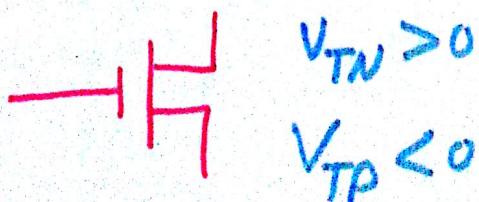
I_{CEO} : base open circuit.

* Breakdown Voltage:

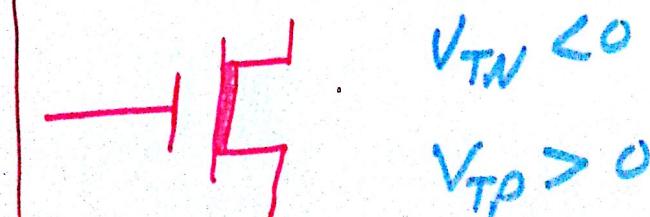
$$BV_{CEO} = \frac{BV_{CBO}}{\sqrt[n]{\beta}}$$

- FET: $I_G = 0$, $I_D = I_S$

* enhancement mode:



* Depletion mode:



* DC analysis: (MOSFET)

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- NMOS:

Non-saturation mode:

Saturation mode:

$$V_{DS} = V_{GS} - V_{TN}$$

$$V_{DS} < V_{DS} \text{ (sat)}$$

↳ for both

$$V_{DS} > V_{DS} \text{ (sat)}$$

$$i_D = K_n [2(V_{GS} - V_{TN})V_{DS} - V_{DS}^2]$$

$$i_D = K_n (V_{GS} - V_{TN})^2$$

- PMOS:

Non-saturation mode:

Saturation mode:

$$V_{SD} = V_{GS} + V_{TP}$$

↳ for both

$$V_{SD} < V_{SD} \text{ (sat)}$$

$$V_{SD} > V_{SD} \text{ (sat)}$$

$$i_D = K_p [2(V_{GS} + V_{TP})V_{SD} - V_{SD}^2]$$

$$i_D = K_p (V_{GS} + V_{TP})^2$$

* DC analysis:

- ① find V_{GS} from input loop.
- ② if $V_{GS} < V_{TN} \Rightarrow$ "Cutoff mode", $I_D = 0$
- ③ if $V_{GS} > V_{TN} \Rightarrow$ assume saturation:
 - ↳ find $i_D = K_n (V_{GS} - V_{TN})^2$
 - ↳ find V_{DS} from output loop.

if $V_{DS} > V_{DS_{(sat)}}$ \Rightarrow "saturation mode"

otherwise: "Non saturation mode".

*Note: C_S & $C_C \Rightarrow$ Become open circuit in DC analysis.

shunt Capacitor Coupling Capacitor.

GOOD
LUCK

